



60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	$8m\Omega$ @ $V_{GS} = 10V$	70A
60V	12mΩ @ V _{GS} = 4.5V	50A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DCDC Converters

Features

- Rated to 175°C ideal for high ambient temperature environments
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low On-Resistance
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

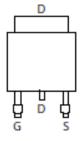
Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.33 grams (Approximate)

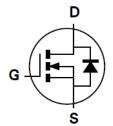




Top View



Pin Out Top View



Equivalent Circuit

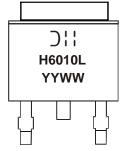
Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH6010LK3Q-13	TO252	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- Automotive products are AEC-Q101 qualified and are PPAP capable. For more information, please refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



] | | = Manufacturer's Marking H6010L = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 15 = 2015) WW = Week Code (01 to 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 6)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	14.8 11.9	А
Continuous Drain Current, V _{GS} = 10V (Note 7)	$T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$	I_D	70 50	Α
Maximum Continuous Body Diode Forward Current (Note 7)	Is	60	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	130	Α	
Avalanche Current, L = 0.1mH	I _{AS}	20	Α	
Avalanche Energy, L = 0.1mH	E _{AS}	20	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	31	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	47	°C/W
Total Power Dissipation (Note 7)	P _D	60	W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	2.5	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +175	°C

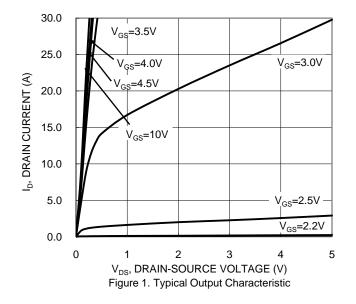
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

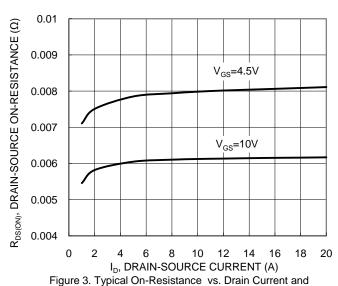
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	-	V	$V_{GS} = 0V$, $I_D = 1mA$	
		-	ı	1	μΑ	$V_{DS} = 48V$, $V_{GS} = 0V$	
Zero Gate Voltage Drain Current (Note 9)	I _{DSS}	1	-	100	μΑ	$V_{DS} = 48V, V_{GS} = 0V,$ $T_{J} = 125^{\circ}C$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		-	6.3	8	mΩ	V _{GS} = 10V, I _D = 20A	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	8.3	12		$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V _{SD}	-	0.9	1.2	V	V _{GS} = 0V, I _S = 20A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	-	2090	-		$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss	-	746	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	38.5	-		1 = 11/11 12	
Gate Resistance	R_g	0.1	0.59	1.8	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	-	19.3	-			
Total Gate Charge (V _{GS} = 10V)	Q_g	-	41.3	-	nC	V 20V I 20A	
Gate-Source Charge	Q_{gs}	-	6	-	110	$V_{DS} = 30V, I_{D} = 20A$	
Gate-Drain Charge	Q_{gd}	-	8.8	-			
Turn-On Delay Time	t _{D(ON)}	-	5.7	-		V _{DD} = 30V, V _{GS} = 10V,	
Turn-On Rise Time	t _R		4.3	1	ns		
Turn-Off Delay Time	t _{D(OFF)}	-	23.4	-	ns	$I_D = 20A$, $R_g = 3\Omega$	
Turn-Off Fall Time	t _F	-	9.7	-			
Body Diode Reverse Recovery Time	t _{RR}	-	35.4	-	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	-	38.2	-	nC	$I_F = 20A$, di/dt = 100A/ μ s	

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.7. Thermal resistance from junction to soldering point (on the exposed drain pad).8. Short duration pulse test used to minimize self-heating effect. Notes:

9. Guaranteed by design. Not subject to product testing.







Gate Voltage

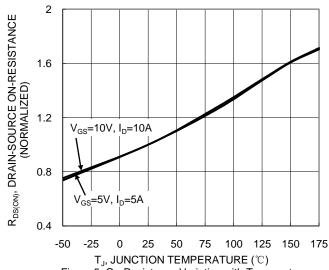


Figure 5. On-Resistance Variation with Temperature

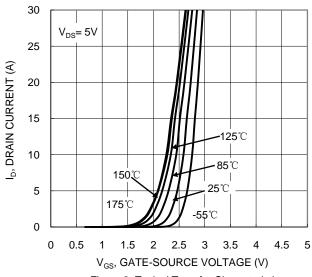


Figure 2. Typical Transfer Characteristic

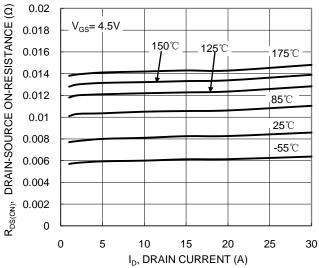


Figure 4. Typical On-Resistance vs. Drain Current and Temperature

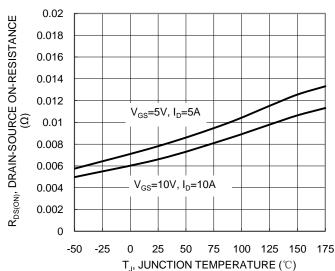
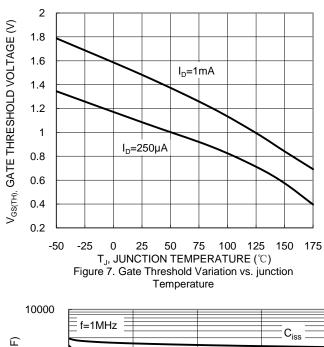
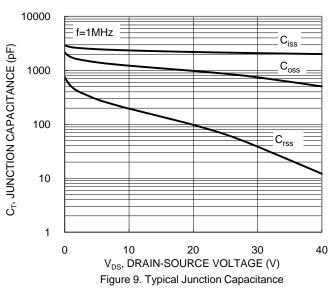
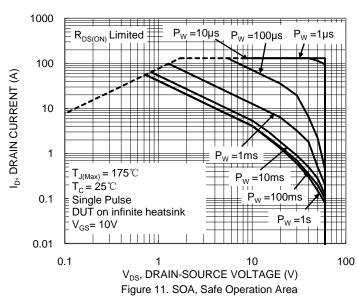


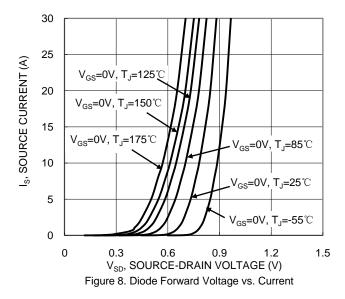
Figure 6. On-Resistance Variation with Temperature

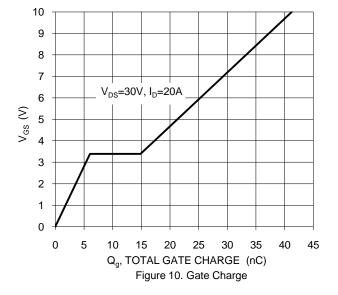














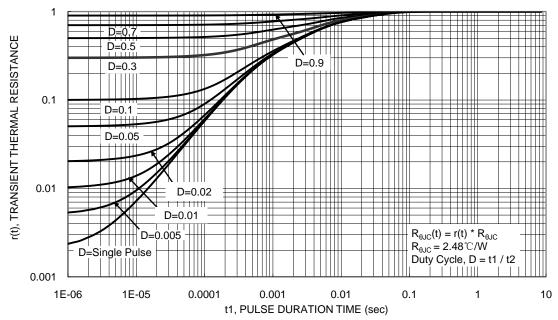
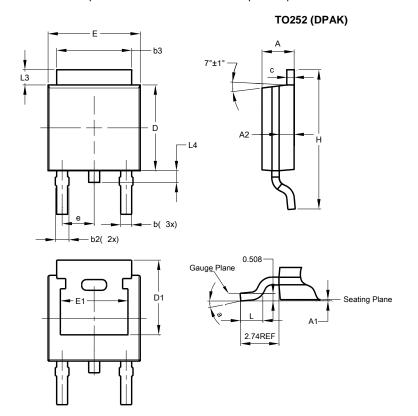


Figure 12 . Transient Thermal Resistance



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

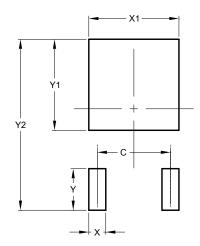


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
C	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
П	6.45	6.70	6.58		
E1	4.32	-	-		
I	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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